



Welcome to [E-XFL.COM](#)

Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8349vvagd

NOTE

The information in this document is accurate for revision 3.x silicon and later (in other words, for orderable part numbers ending in A or B). For information on revision 1.1 silicon and earlier versions, see the *MPC8349E PowerQUICC II Pro Integrated Host Processor Hardware Specifications*.

See [Section 22.1, “Part Numbers Fully Addressed by This Document,”](#) for silicon revision level determination.

1 Overview

This section provides a high-level overview of the device features. [Figure 1](#) shows the major functional units within the MPC8349EA.

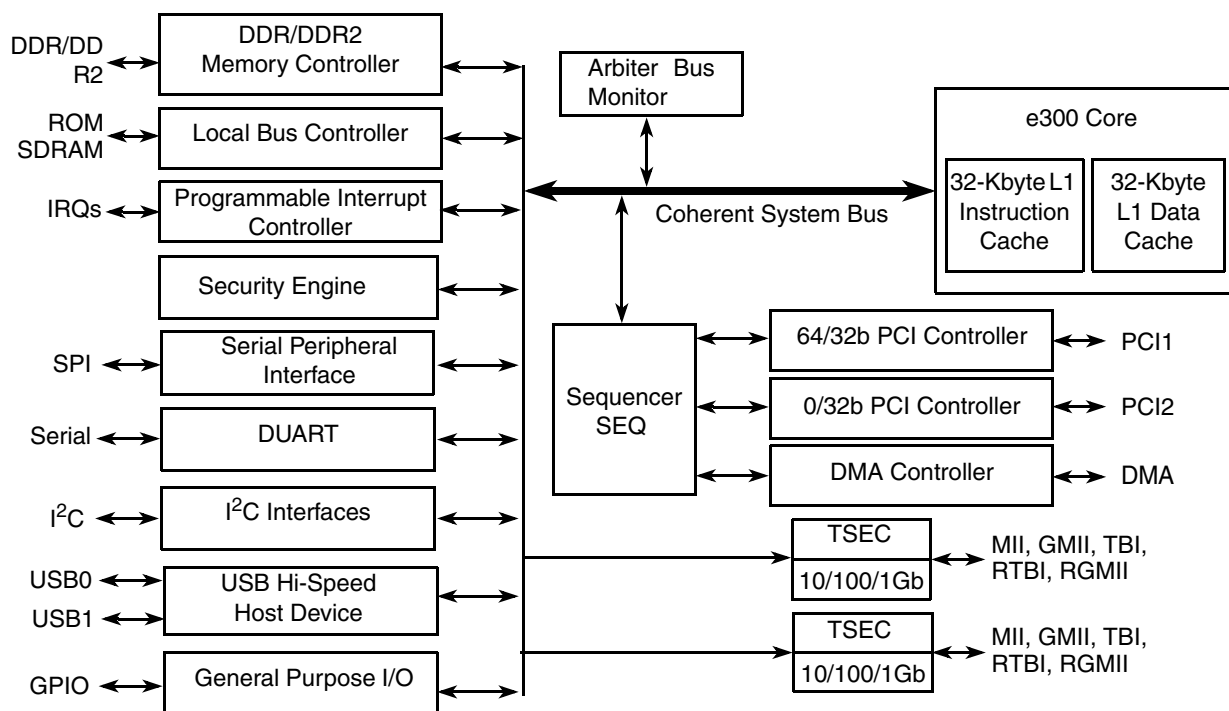


Figure 1. MPC8349EA Block Diagram

Major features of the device are as follows:

- Embedded PowerPC e300 processor core; operates at up to 667 MHz
 - High-performance, superscalar processor core
 - Floating-point, integer, load/store, system register, and branch processing units
 - 32-Kbyte instruction cache, 32-Kbyte data cache
 - Lockable portion of L1 cache
 - Dynamic power management
 - Software-compatible with the other Freescale processor families that implement Power Architecture technology

- Double data rate, DDR1/DDR2 SDRAM memory controller
 - Programmable timing supporting DDR1 and DDR2 SDRAM
 - 32- or 64-bit data interface, up to 400 MHz data rate
 - Up to four physical banks (chip selects), each bank up to 1 Gbyte independently addressable
 - DRAM chip configurations from 64 Mbits to 1 Gbit with $\times 8/\times 16$ data ports
 - Full error checking and correction (ECC) support
 - Support for up to 16 simultaneous open pages (up to 32 pages for DDR2)
 - Contiguous or discontiguous memory mapping
 - Read-modify-write support
 - Sleep-mode support for SDRAM self refresh
 - Auto refresh
 - On-the-fly power management using CKE
 - Registered DIMM support
 - 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- Dual three-speed (10/100/1000) Ethernet controllers (TSECs)
 - Dual controllers designed to comply with IEEE 802.3TM, 802.3uTM, 802.3xTM, 802.3zTM, 802.3acTM standards
 - Ethernet physical interfaces:
 - 1000 Mbps IEEE Std. 802.3 GMII/RGMII, IEEE Std. 802.3z TBI/RTBI, full-duplex
 - 10/100 Mbps IEEE Std. 802.3 MII full- and half-duplex
 - Buffer descriptors are backward-compatible with MPC8260 and MPC860T 10/100 programming models
 - 9.6-Kbyte jumbo frame support
 - RMON statistics support
 - Internal 2-Kbyte transmit and 2-Kbyte receive FIFOs per TSEC module
 - MII management interface for control and status
 - Programmable CRC generation and checking
- Dual PCI interfaces
 - Designed to comply with *PCI Specification Revision 2.3*
 - Data bus width options:
 - Dual 32-bit data PCI interfaces operating at up to 66 MHz
 - Single 64-bit data PCI interface operating at up to 66 MHz
 - PCI 3.3-V compatible
 - PCI host bridge capabilities on both interfaces
 - PCI agent mode on PCI1 interface
 - PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses and support for delayed read transactions
 - Posting of processor-to-PCI and PCI-to-memory writes

- Dual industry-standard I²C interfaces
 - Two-wire interface
 - Multiple master support
 - Master or slave I²C mode support
 - On-chip digital filtering rejects spikes on the bus
 - System initialization data optionally loaded from I²C-1 EPROM by boot sequencer embedded hardware
- DMA controller
 - Four independent virtual channels
 - Concurrent execution across multiple channels with programmable bandwidth control
 - Handshaking (external control) signals for all channels: `DMA_DREQ[0:3]`, `DMA_DACK[0:3]`, `DMA_DDONE[0:3]`
 - All channels accessible to local core and remote PCI masters
 - Misaligned transfer capability
 - Data chaining and direct mode
 - Interrupt on completed segment and chain
- DUART
 - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Serial peripheral interface (SPI) for master or slave
- General-purpose parallel I/O (GPIO)
 - 64 parallel I/O pins multiplexed on various chip interfaces
- System timers
 - Periodic interrupt timer
 - Real-time clock
 - Software watchdog timer
 - Eight general-purpose timers
- Designed to comply with IEEE Std. 1149.1™, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8349EA. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings¹

Parameter		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.32 (1.36 max for 667-MHz core frequency)	V	—
PLL supply voltage		AV_{DD}	–0.3 to 1.32 (1.36 max for 667-MHz core frequency)	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63	V	—
PCI, local bus, DUART, system control and power management, I ² C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to ($GV_{DD} + 0.3$)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to ($GV_{DD} + 0.3$)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to ($LV_{DD} + 0.3$)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I ² C, and JTAG signals	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	3, 5
	PCI	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

- ¹ Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- ² **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ³ **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ⁴ **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ⁵ (M,L,O) V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
- ⁶ OV_{IN} on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

Table 19 provides the input AC timing specifications for the DDR SDRAM interface.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of $(1.8 \text{ or } 2.5 \text{ V}) \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC/MDM	t_{CISKEW}			ps	1, 2
400 MHz		–600	600		3
333 MHz		–750	750		—
266 MHz		–750	750		—
200 MHz		–750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW} . This can be determined by the equation: $t_{DISKEW} = \pm (T/4 - \text{abs}(t_{CISKEW}))$; where T is the clock period and $\text{abs}(t_{CISKEW})$ is the absolute value of t_{CISKEW} .
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

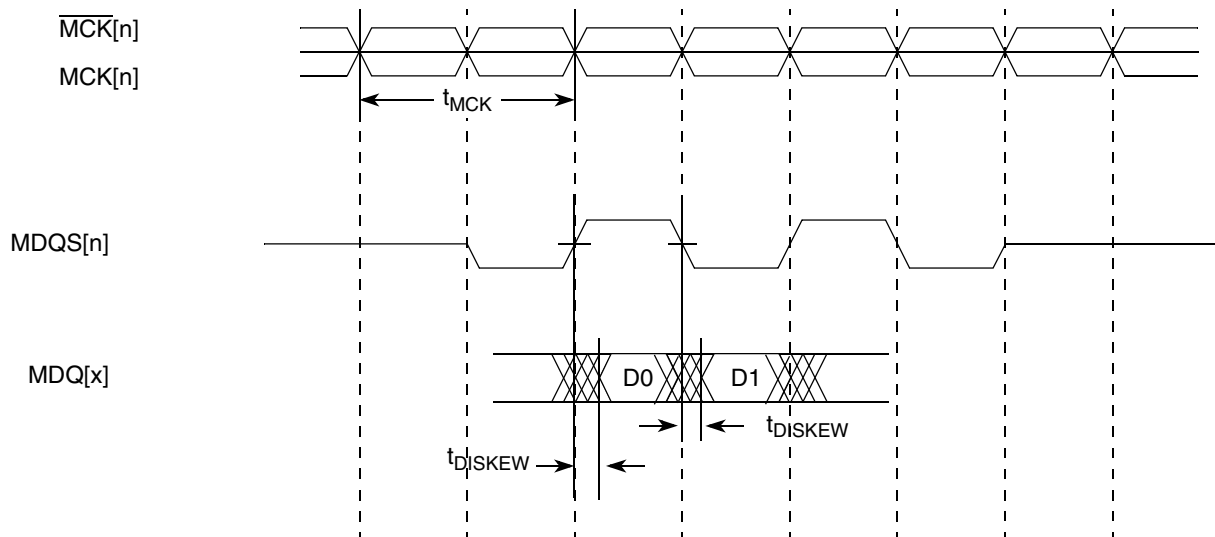


Figure 5. DDR Input Timing Diagram

8.2.1.1 GMII Transmit AC Timing Specifications

Table 25 provides the GMII transmit AC timing specifications.

Table 25. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{GTXH}/t_{GTX}	43.75	—	56.25	%
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.5	—	5.0	ns
GTX_CLK clock rise time (20%–80%)	t_{GTXR}	—	—	1.0	ns
GTX_CLK clock fall time (80%–20%)	t_{GTXF}	—	—	1.0	ns

Notes:

- The symbols for timing specifications follow the pattern $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTXR} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 9 shows the GMII transmit AC timing diagram.

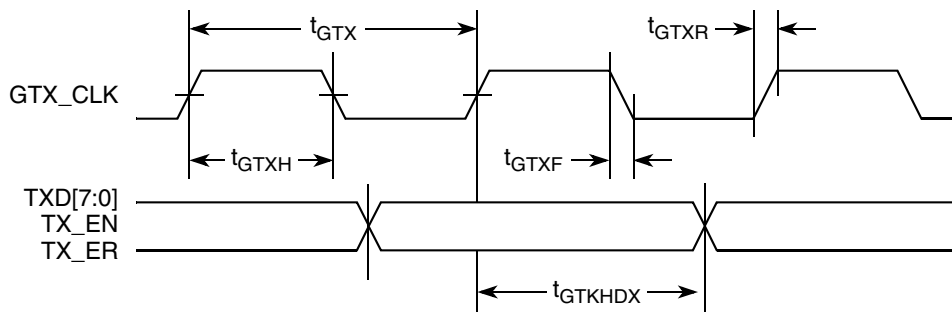


Figure 9. GMII Transmit AC Timing Diagram

8.2.1.2 GMII Receive AC Timing Specifications

Table 26 provides the GMII receive AC timing specifications.

Table 26. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.5	—	—	ns

Table 28. MII Receive AC Timing Specifications (continued)At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock rise (20%–80%)	t_{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time (80%–20%)	t_{MRXF}	1.0	—	4.0	ns

Note:

- The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 12 provides the AC test load for TSEC.

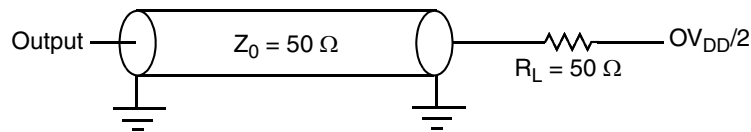
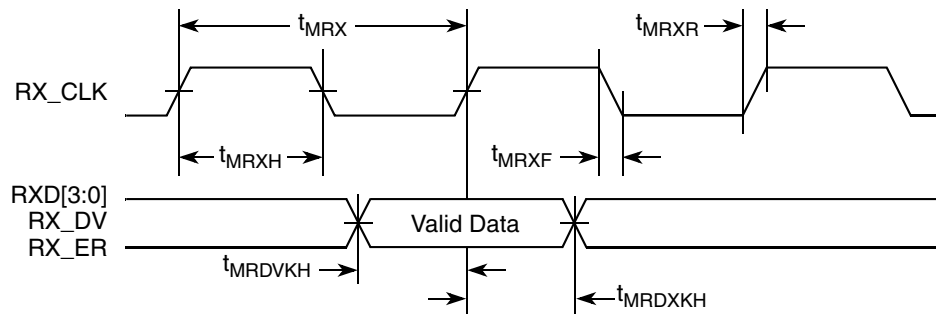
**Figure 12. TSEC AC Test Load**

Figure 13 shows the MII receive AC timing diagram.

**Figure 13. MII Receive AC Timing Diagram**

8.2.3 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8349EA.

9.1 USB DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the USB interface.

Table 35. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	-0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, $I_{OH} = -100\ \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100\ \mu A$	V_{OL}	—	0.2	V

9.2 USB AC Electrical Specifications

Table 36 describes the general timing parameters of the USB interface of the MPC8349EA.

Table 36. USB General Timing Parameters (ULPI Mode Only)

Parameter	Symbol ¹	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	15	—	ns	2–5
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	2–5
Input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	2–5
USB clock to output valid—all outputs	$t_{USKH OV}$	—	7	ns	2–5
Output hold from USB clock—all outputs	$t_{USKH OX}$	2	—	ns	2–5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, $t_{USKH OX}$ symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

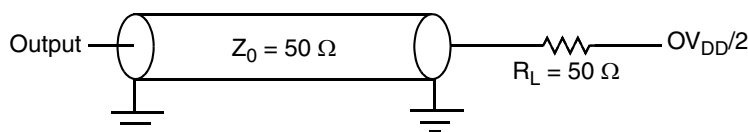
Table 39. Local Bus General Timing Parameters—DLL Bypass⁹

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to output valid	t_{LBKLOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to the falling edge of LCLK0 (for all outputs and for \overline{LGTA} and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin equals to the load on the LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 20 provides the AC test load for the local bus.

**Figure 20. Local Bus C Test Load**

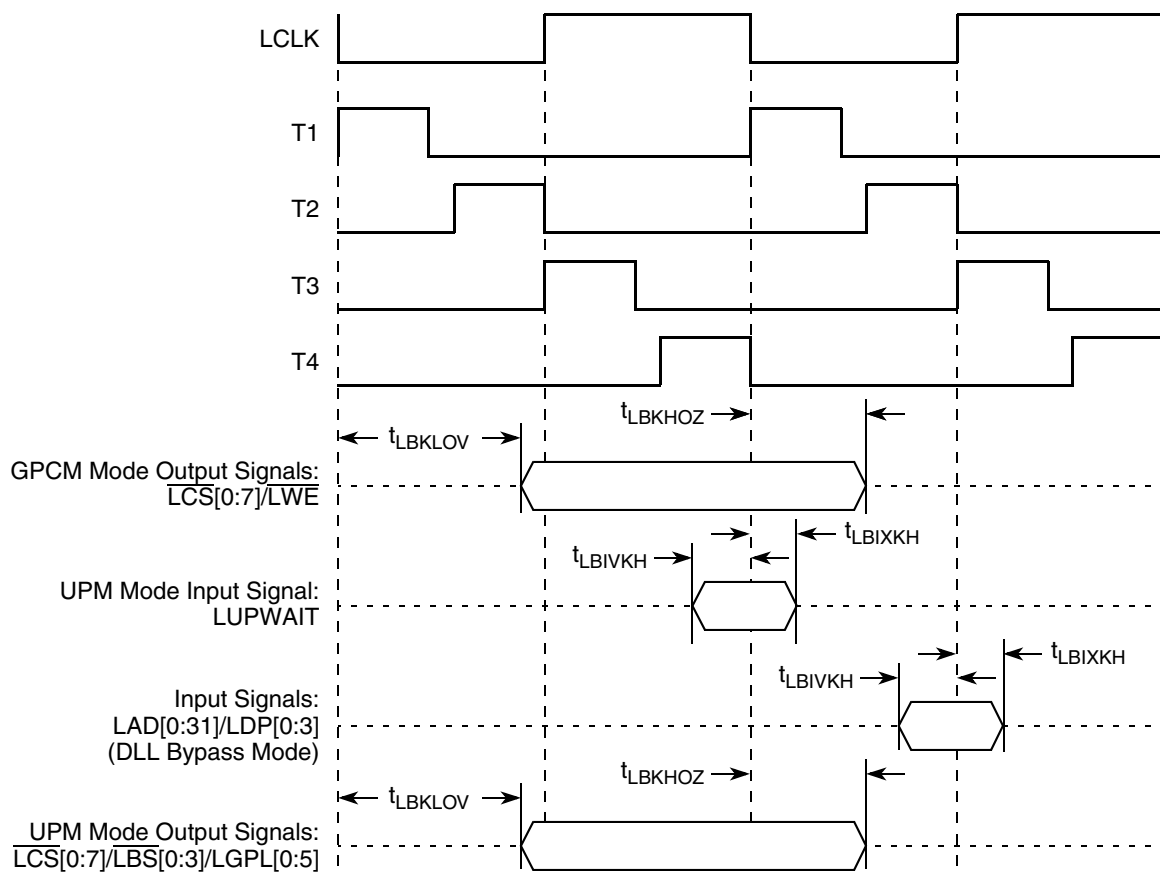


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)

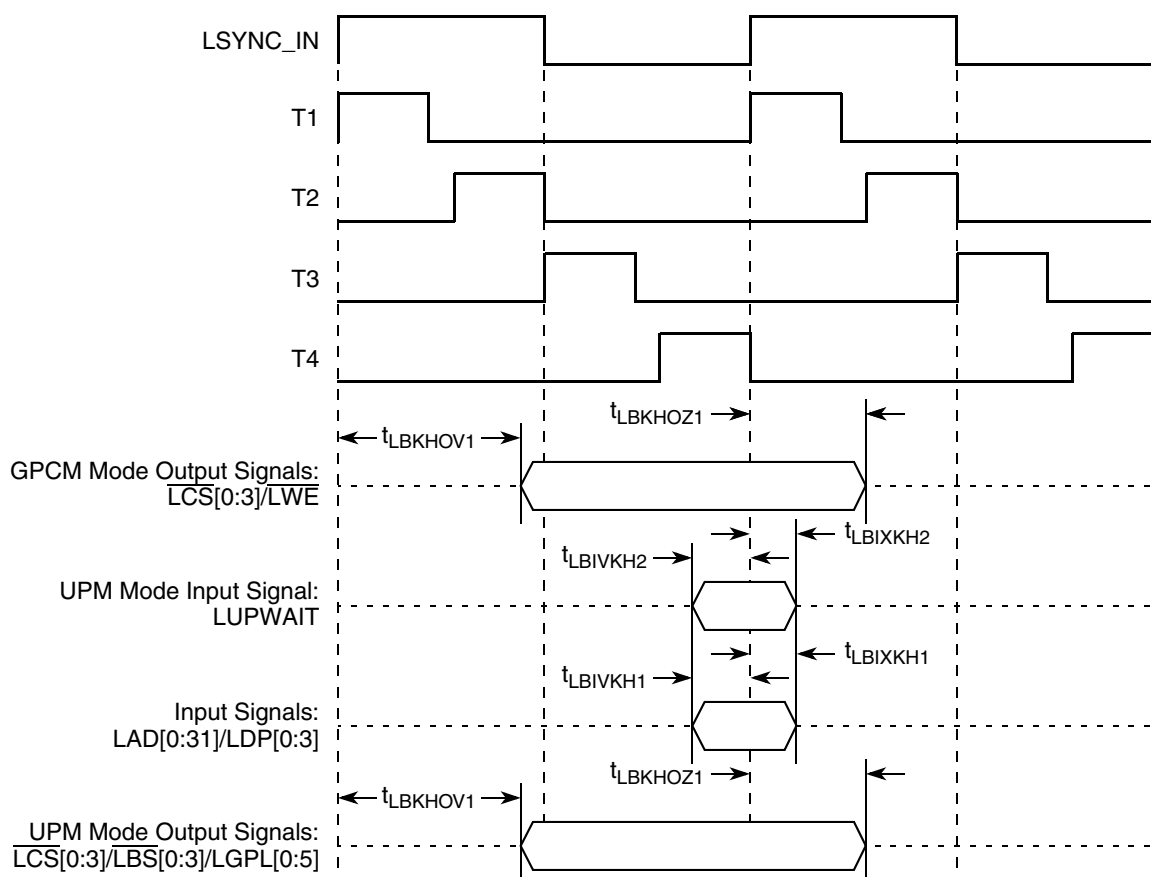


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Enabled)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

11.1 JTAG DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

Table 40. JTAG Interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	$OV_{DD} - 0.3$	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	—	—	± 5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V

Table 40. JTAG Interface DC Electrical Characteristics (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

11.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA. Table 41 provides the JTAG AC timing specifications as defined in Figure 28 through Figure 31.

Table 41. JTAG AC Timing Specifications (Independent of CLKIN)¹

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR}, t_{JTGF}	0	2	ns	—
\overline{TRST} assert time	t_{TRST}	25	—	ns	3
Input setup times:				ns	
Boundary-scan data TMS, TDI	t_{JTDVKH} t_{JTIVKH}	4 4	— —		4
Input hold times:				ns	
Boundary-scan data TMS, TDI	t_{JTDXKH} t_{JTIXKH}	10 10	— —		4
Valid times:				ns	
Boundary-scan data TDO	t_{JTKLDV} t_{JTKLOV}	2 2	11 11		5
Output hold times:				ns	
Boundary-scan data TDO	t_{JTKLDX} t_{JTKLOX}	2 2	— —		5

12 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8349EA.

12.1 I²C DC Electrical Characteristics

Table 42 provides the DC electrical characteristics for the I²C interface of the MPC8349EA.

Table 42. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	-0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from $V_{IH}(\text{min})$ to $V_{IL}(\text{max})$ with a bus capacitance from 10 to 400 pF	t_{12KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{12KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}(\text{max})$)	I_I	-10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8349EA Integrated Host Processor Family Reference Manual*, for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I²C AC Electrical Specifications

Table 43 provides the AC timing parameters for the I²C interface of the MPC8349EA. Note that all values refer to $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$ levels (see Table 42).

Table 43. I²C AC Electrical Specifications

Parameter	Symbol ¹	Min	Max	Unit
SCL clock frequency	f_{12C}	0	400	kHz
Low period of the SCL clock	t_{12CL}	1.3	—	μs
High period of the SCL clock	t_{12CH}	0.6	—	μs
Setup time for a repeated START condition	t_{12SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{12SXKL}	0.6	—	μs
Data setup time	t_{12DVKH}	100	—	ns
Data hold time: CBUS compatible masters I ² C bus devices	t_{12DXKL}	— 0 ²	— 0.9 ³	μs

Figure 34 provides the AC test load for PCI.

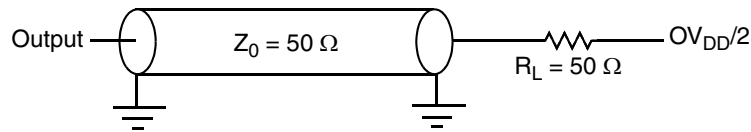


Figure 34. PCI AC Test Load

Figure 35 shows the PCI input AC timing diagram.

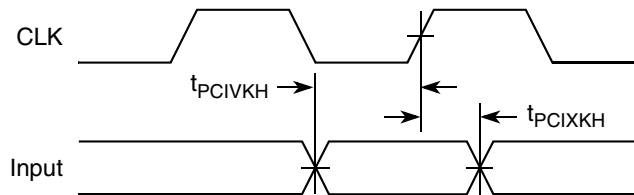


Figure 35. PCI Input AC Timing Diagram

Figure 36 shows the PCI output AC timing diagram.

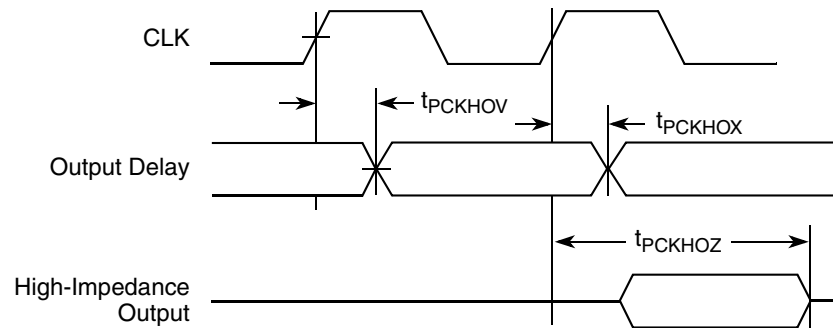


Figure 36. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 47 provides the DC electrical characteristics for the MPC8349EA timer pins, including T_{IN} , \overline{TOUT} , \overline{TGATE} , and RTC_CLK .

Table 47. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	—	—	± 5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V

Table 47. Timer DC Electrical Characteristics (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

14.2 Timer AC Timing Specifications

Table 48 provides the timer input and output AC timing specifications.

Table 48. Timers Input AC Timing Specifications¹

Parameter	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 49 provides the DC electrical characteristics for the MPC8349EA GPIO.

Table 49. GPIO DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	−0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC2_TX_ER/GPIO1[24]	F14	I/O	OV _{DD}	—
TSEC2_TX_EN/GPIO1[12]	C5	I/O	LV _{DD2}	—
TSEC2_TX_CLK/GPIO1[30]	E14	I/O	OV _{DD}	—
UART				
UART_SOUT[1:2]/MSRCID[0:1]/LSRCID[0:1]	AK27, AN29	O	OV _{DD}	—
UART_SIN[1:2]/MSRCID[2:3]/LSRCID[2:3]	AL28, AM29	I/O	OV _{DD}	—
UART_CTS[1]/MSRCID4/LSRCID4	AP30	I/O	OV _{DD}	—
UART_CTS[2]/MDVAL/ LDVAL	AN30	I/O	OV _{DD}	—
UART_RTS[1:2]	AP31, AM30	O	OV _{DD}	—
I²C interface				
IIC1_SDA	AK29	I/O	OV _{DD}	2
IIC1_SCL	AP32	I/O	OV _{DD}	2
IIC2_SDA	AN31	I/O	OV _{DD}	2
IIC2_SCL	AM31	I/O	OV _{DD}	2
SPI				
SPIMOSI/LCS[6]	AN32	I/O	OV _{DD}	—
SPIMISO/LCS[7]	AP33	I/O	OV _{DD}	—
SPICLK	AK30	I/O	OV _{DD}	—
SPISEL	AL31	I	OV _{DD}	—
Clocks				
PCI_CLK_OUT[0:2]	AN9, AP9, AM10,	O	OV _{DD}	—
PCI_CLK_OUT[3]/LCS[6]	AN10	O	OV _{DD}	—
PCI_CLK_OUT[4]/LCS[7]	AJ11	O	OV _{DD}	—
PCI_CLK_OUT[5:7]	AP10, AL11, AM11	O	OV _{DD}	—
PCI_SYNC_IN/PCI_CLOCK	AK12	I	OV _{DD}	—
PCI_SYNC_OUT	AP11	O	OV _{DD}	3
RTC/PIT_CLOCK	AM32	I	OV _{DD}	—
CLKIN	AM9	I	OV _{DD}	—
JTAG				
TCK	E20	I	OV _{DD}	—
TDI	F20	I	OV _{DD}	4

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GND	A1, A34, C1, C7, C10, C11, C15, C23, C25, C28, D1, D8, D20, D30, E7, E13, E15, E17, E18, E21, E23, E25, E32, F6, F19, F27, F30, F34, G31, H5, J4, J34, K30, L5, M2, M5, M30, M33, N3, N5, P30, R5, R32, T5, T30, U6, U29, U33, V2, V5, V30, W6, W30, Y30, AA2, AA30, AB2, AB6, AB30, AC3, AC6, AD31, AE5, AF2, AF5, AF31, AG30, AG31, AH4, AJ3, AJ19, AJ22, AK7, AK13, AK14, AK16, AK18, AK20, AK25, AK28, AL3, AL5, AL10, AL12, AL22, AL27, AM1, AM6, AM7, AN12, AN17, AN34, AP1, AP8, AP34	—	—	—
GV _{DD}	A2, E2, G5, G6, J5, K4, K5, L4, N4, P5, R6, T6, U5, V1, W5, Y5, AA4, AB3, AC4, AD5, AF3, AG5, AH2, AH5, AH6, AJ6, AK6, AK8, AK9, AL6	Power for DDR DRAM I/O voltage (2.5 V)	GV _{DD}	—
LV _{DD1}	C9, D11	Power for three speed Ethernet #1 and for Ethernet management interface I/O (2.5 V, 3.3 V)	LV _{DD1}	—
LV _{DD2}	C6, D9	Power for three speed Ethernet #2 I/O (2.5 V, 3.3 V)	LV _{DD2}	—
V _{DD}	E19, E29, F7, F9, F11, F13, F15, F17, F18, F21, F23, F25, F29, H29, J6, K29, M29, N6, P29, T29, U30, V6, V29, W29, AB29, AC5, AD29, AF6, AF29, AH29, AJ8, AJ12, AJ14, AJ16, AJ18, AJ20, AJ21, AJ23, AJ25, AJ26, AJ27, AJ28, AJ29, AK10	Power for core (1.2 V nominal, 1.3 V for 667 MHz)	V _{DD}	—
OV _{DD}	B22, B28, C16, C17, C24, C26, D13, D15, D19, D29, E31, F28, G33, H30, L29, L32, N32, P31, R31, U32, W31, Y29, AA29, AC30, AE31, AF30, AG29, AJ17, AJ30, AK11, AL15, AL19, AL21, AL29, AL30, AM20, AM23, AM24, AM26, AM28, AN11, AN13	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV _{DD}	—
MVREF1	M3	I	DDR reference voltage	—

(edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

20.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

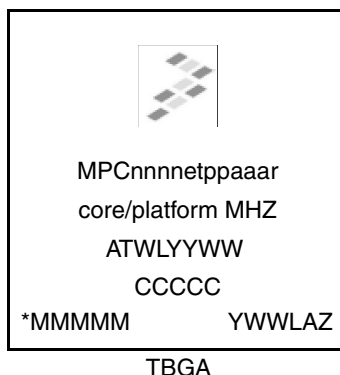
20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

22.2 Part Marking

Parts are marked as in the example shown in [Figure 44](#).



Notes:

ATWLYYWW is the traceability code.

CCCCC is the country code.

MMMMM is the mask number.

YWWLAZ is the assembly traceability code.

Figure 44. Freescale Part Marking for TBGA Devices

23 Document Revision History

This table provides a revision history of this document.

Table 68. Document Revision History

Rev. Number	Date	Substantive Change(s)
13	09/2011	<ul style="list-style-type: none"> In Section 2.2, "Power Sequencing," added Section 2.2.1, "Power-Up Sequencing" and Figure 4. In Table 25, Table 29 and Table 31, removed the GTX_CLK125. In Table 34, updated t_{MDKHDX} Max value from 170ns to 70ns.
12	11/2010	<ul style="list-style-type: none"> In Table 55 added note for pin LGPL4. In Section 21.7, "Pull-Up Resistor Requirements," updated the list of open drain type pins.
11	05/2010	<ul style="list-style-type: none"> In Table 25 through Table 30, changed $V_{IL}(\min)$ to $V_{IH}(\max)$ to (20%–80%). Added Table 8, "EC GTX_CLK125 AC Timing Specifications."
10	5/2009	<ul style="list-style-type: none"> In Table 57, updated frequency for max csb_clk to 333 MHz and DDR2, from 100-200 to 100-133 at core frequency = 533MHz. In Section 18.1, "Package Parameters for the MPC8349EA TBGA," changed solder ball for TBGA and PBGA from 95.5 Sn/0.5 Cu/4 Ag to 96.5 Sn/3.5 Ag. In Table 66, footnote 1, changed 667(TBGA) to 533(TBGA). footnote 4, added data rate for DDR1 and DDR2.

Table 68. Document Revision History (continued)

Rev. Number	Date	Substantive Change(s)
3	11/2006	<ul style="list-style-type: none"> Updated note in introduction. In the features list in Section 1, "Overview," updated DDR data rate to show 400 MHz for DDR2 for TBGA parts for silicon 3.x and 400 MHz for DDR2 for TBGA parts for silicon 3.x. In Section 23, "Ordering Information," replicated note from document introduction.
2	8/2006	<ul style="list-style-type: none"> Changed all references to revision 2.0 silicon to revision 3.0 silicon. Changed VIH minimum value in Table 40, "JTAG Interface DC Electrical Characteristics," to $OV_{DD} - 0.3$. In Table 44, "PCI DC Electrical Characteristics," changed high-level input voltage values to min = 2 and max = $OV_{DD} + 0.3$; changed low-level input voltage values to min = (-0.3) and max = 0.8. Updated DDR2 I/O power values in Table 5, "MPC8347EA Typical I/O Power Dissipation." In Table 66, "Suggested PLL Configurations," deleted reference-number rows 902 and 703.
1	4/2006	<ul style="list-style-type: none"> Removed Table 20, "Timing Parameters for DDR2-400." Changed ADDR/CMD to ADDR/CMD/MODT in Table 9, "DDR and DDR2 SDRAM Output AC Timing Specifications," rows 2 and 3, and in Figure 2, "DDR SDRAM Output Timing Diagram." Changed Min and Max values for V_{IH} and V_{IL} in Table 40Table 44, "PCI DC Electrical Characteristics." In Table 55, "MPC8349EA (TBGA) Pinout Listing," and Table 52, "MPC8347EA (PBGA) Pinout Listing," modified rows for MDICO and MDIC1 signals and added note 'It is recommended that MDICO be tied to GRD using an 18 Ω resistor and MCIC1 be tied to DDR power using an 18 Ω resistor.' Table 55, "MPC8349EA (TBGA) Pinout Listing," in row AVDD3 changed power supply from "AVDD3" to '—.'
0	3/2006	Initial public release